



500V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -500V
- I_C = -150mA High Continuous Current
- I_{CM} = -500mA Peak Pulse Current
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXTP01500BGQ)

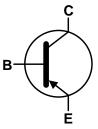
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208⁽²⁾
- Weight: 0.112 grams (Approximate)

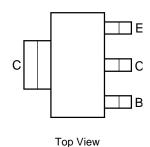








Device Symbol



Pin-Out

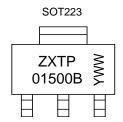
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP01500BGTC	Standard	ZXTP 01500B	13	12	4,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



ZXTP01500B = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 9 = 2019) WW or \overline{WW} = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-500	V
Collector-Emitter Voltage	V _{CEO}	-500	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-150	mA
Peak Pulse Current	I _{CM}	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	р	2	W
Power Dissipation	(Note 6)	P_{D}	3	W
Thermal Decistores, Junction to Ambient	(Note 5)		62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)		R _{0JL}	14.8	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 25mm × 25mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.

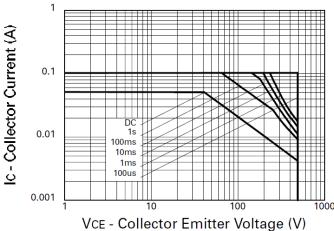
 6. Same as note (5), except the device is mounted on 50mm × 50mm 2oz copper.

 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

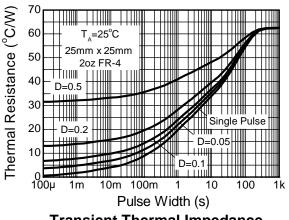
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



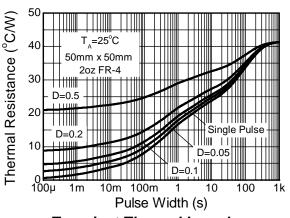
Thermal Characteristics and Derating Information



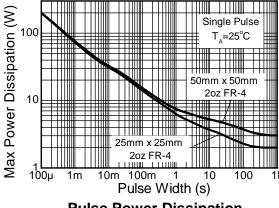
Safe Operating Area



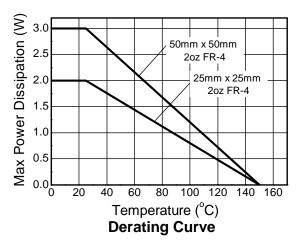
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation





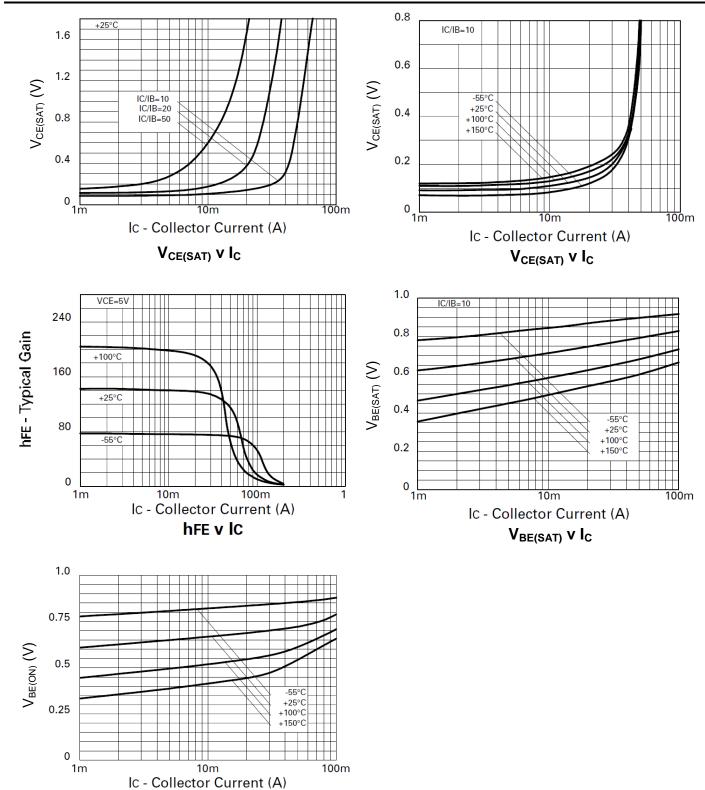
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-500	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-500	_	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	_	_	-100	nA	V _{CB} = -500V
Collector Cut-Off Current	I _{CES}	_	_	-100	nA	V _{CE} = -500V
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -5.6V
Collector Emitter Seturation Valtage (Note 0)	M	_	_	-200	mV	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE} (SAT)	_	_	-500	mv	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	_	-900	mV	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	_	-900	mV	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$
		100	_	300		$I_C = -1mA$, $V_{CE} = -10V$
DC Current Gain (Note 9)	h _{FE}	80	_	300	_	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$
		_	15	_		I _C = -100mA, V _{CE} = -10V
Current Gain-Bandwidth Product	f⊤	60	_	_	MHz	$V_{CE} = -20V, I_{C} = -10mA$ f = 50MHz
Turn-On Time	t _{ON}	_	110	_	ns	V _{CC} = -100V, I _C = -50mA
Turn-Off Time	t _{OFF}	_	1.5	_	μs	$I_{B1} = -5mA$, $I_{B2} = 10mA$
Output Capacitance	Сово	_	_	8	pF	V _{CB} = -20V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



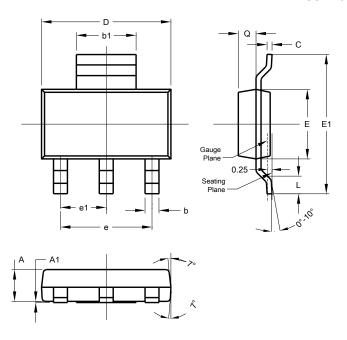
 $V_{BE(ON)} v I_C$



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

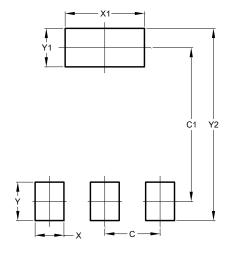


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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